







CD54HC173, CD74HC173, CD54HCT173, CD74HCT173 SCHS158F - NOVEMBER 1998 - REVISED MARCH 2022

CDx4HC173, CDx4HCT173 High-Speed CMOS Logic Quad D-Type Flip-Flop, Three-State

1 Features

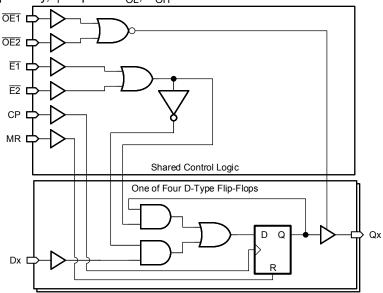
- Three-state buffered outputs
- Gated input and output enables
- Fanout (over temperature range)
 - Standard outputs : 10 LSTTL loads Bus driver outputs : 15 LSTTL loads
- Wide Operating Temperature Range : -55°C to ٠ 125°C
- Balanced propagation delay and transition times
- Significant power and reduction compared to • LSTTL logic ICs
- HC types
 - 2 V to 6 V operation
 - High noise immunity: $N_{II} = 30\%$, $N_{IH} = 30\%$ of V_{CC} at V_{CC} = 5 V
- HCT types
 - 4.5 V to 5.5 V Operation
 - Direct LSTTL input logic compatibility, V_{II} = 0.8 V (Max), $V_{IH} = 2 V$ (Min)
 - CMOS input compatibility, $I_I \leq 1\mu A$ at V_{OI} , V_{OH}

2 Description

The CDx4HC173 and CDx4HCT173 contains four independent D-type flip-flops with shared clock (CP), reset (MR), and data enable ($\overline{E1}$, $\overline{E2}$) pins.

Device Information									
PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)							
CD54HC173F	CDIP (16)	21.34 mm × 6.92 mm							
CD54HCT173F3A	CDIP (16)	21.34 mm × 6.92 mm							
CD74HC173E	PDIP (16)	19.31mm × 6.35 mm							
CD74HCT173E	PDIP (16)	19.31mm × 6.35 mm							
CD74HC173M	SOIC (16)	9.90 mm × 3.90 mm							
CD74HCT173M	SOIC (16)	9.90 mm × 3.90 mm							
CD74HC173PW	TSSOP (16)	5.00 mm × 4.40 mm							

(1) For all packages see the orderable addendum at the end of the data sheet ...



Functional Block Diagram





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7.1 Overview	Information

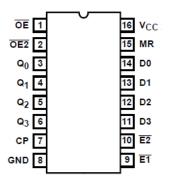
3 Revision History

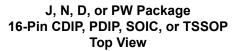
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

C	hanges from Revision E (October 2003) to Revision F (March 2022)	Page
•	Updated the numbering, formatting, tables, figures, and cross-references throughout the document to re	eflect
	modern data sheet standards	1



4 Pin Configuration and Functions







5 Specifications

5.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage		-0.5	7	V
I _{IK}	Input diode current ⁽²⁾	$V_{\rm I} < -0.5$ V or $V_{\rm I} > V_{\rm CC} + 0.5$ V		±20	mA
Ι _{ΟΚ}	Output diode current ⁽²⁾	$V_{\rm O}$ < -0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V		±20	mA
lo	Output source or sink current per output pin		±25	mA	
	Continuous current through V_{CC} or GND			±70	mA
TJ	Junction temperature			150	°C
	Lead temperature (soldering 10s) (SOIC - lead		300	°C	
T _{stg}	Storage temperature		-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Rating may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Condition. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 Recommended Operating Conditions

			MIN	MAX	UNIT	
V	Supply voltage range	HC types	2	6	V	
V _{CC}	Supply voltage range	HCT types	4.5	5.5	v	
VI	Input voltage	Input voltage				
Vo	Output voltage	Output voltage				
		V _{CC} = 2V		1000		
t _t	Input rise and fall time	V _{CC} = 4.5V		500	ns	
		V _{CC} = 6V		400		
T _A	Temperature range	-55	125	°C		

5.3 Thermal Information

		N (PDIP)	D (SOIC)	NS (SOP)	PW (TSSOP)	
	THERMAL METRIC	16 PINS	16 PINS	16 PINS	16 PINS	UNIT
R _{θJA}	Junction-to-ambient thermal resistance ⁽¹⁾	67	73	64	108	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report



5.4 Electrical Characteristics

	PARAMETER	TEST	V		25°C		–40°C t	o 85°C	–55°C to 125°C		UNIT	
	PARAMETER	CONDITIONS ⁽¹⁾	V _{cc}	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT	
HC TYPES	3											
			2	1.5			1.5		1.5		V	
V _{IH}	High-level input voltage		4.5	3.15			3.15		3.15		V	
			6	4.2			4.2		4.2		V	
			2			0.5		0.5		0.5	V	
V _{IL}	Low-level input voltage		4.5			1.35		1.35		1.35	V	
			6			1.8		1.8		1.8	V	
	High-level output voltage	Ι _{ΟΗ} = – 20μΑ	2	1.9			1.9		1.9		V	
	CMOS loads	I _{OH} = – 20μA	4.5	4.4			4.4		4.4		V	
V _{OH}		Ι _{ΟΗ} = – 20μΑ	6	5.9			5.9		5.9		V	
	High-level output voltage	I _{OH} = - 6mA	4.5	3.98			3.84		3.7		V	
	TTL loads	I _{OH} = – 7.8mA	6	5.48			5.34		5.2		V	
	Low-level output voltage	Ι _{ΟL} = 20μΑ	2			0.1		0.1		0.1	V	
	CMOS loads	I _{OL} = 20μA	4.5			0.1		0.1		0.1	V	
V _{OL}		I _{OL} = 20μA	6			0.1		0.1		0.1	V	
	Low-level output voltage	I _{OL} = 6mA	4.5			0.26		0.33		0.4	V	
	TTL loads	I _{OL} = 7.8mA	6			0.26		0.33		0.4	V	
l _l	Input leakage current	V _{CC} or GND	6			±0.1		±1		±1	μA	
I _{CC}	Supply current	V _{CC} or GND	6			8		80		160	μA	
I _{OZ}	Three-state leakage current		6			±0.5		±0.5		±10	μA	
НСТ ТҮРЕ	S											
V _{IH}	High-level input voltage		4.5 to 5.5	2			2		2		V	
V _{IL}	Low-level input voltage		4.5 to 5.5			0.8		0.8		0.8	V	
	High-level output voltage CMOS loads	I _{OH} = – 20μΑ	4.5	4.4			4.4		4.4		V	
V _{OH}	High-level output voltage TTL loads	I _{OH} = – 6mA	4.5	3.98			3.84		3.7		V	
	Low-level output voltage CMOS loads	Ι _{ΟL} = 20μΑ	4.5			0.1		0.1		0.1	V	
V _{OL}	Low-level output voltage TTL loads	I _{OL} = 6mA	4.5			0.26		0.33		0.4	V	
lı –	Input leakage current	V _{CC} and GND	5.5			±0.1		±1		±1	μA	
I _{CC}	Supply Current	V _{CC} and GND	5.5			8		80		160	μΑ	
-		One of D0-D3	4.5 to 5.5		15	54		67.5		73.5	μA	
		One of $\overline{E1}$ and $\overline{E2}$	4.5 to 5.5		15	54		67.5		73.5	μA	
ΔI _{CC} ⁽²⁾ (3)	Additional supply current per input pin	СР	4.5 to 5.5		25	90		112.5		122.5	μA	
		MR	4.5 to 5.5		20	72		90		98	μA	
		One of OE1 and OE2	4.5 to 5.5		50	180		225		245	μA	

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	PARAMETER		TEST		25°C			–40°C to 85°C		–55°C to 125°C		UNIT
			CONDITIONS ⁽¹⁾	V _{cc}	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
lo	7	Three-state leakage current		5.5			±0.5		±5.0		±10	μA

(1) $V_I = V_{IH}$ or V_{IL} , unless otherwise noted.

(2) For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

(3) Inputs held at $V_{CC} - 2.1$.

5.5 Switching Characteristics

Input t_t = 6ns. Unless otherwise specified, C_L = 50pF

	PARAMETER	V _{cc} (V)	25°C		-40°C to 85°C	-55°C to 125°C	UNIT	
			ТҮР	MAX	MAX	MAX		
HC TYPES								
		2		200	250	300		
t _{pd}	Propagation delay, clock to output	4.5	17 ⁽¹⁾	40	50	60	ns	
		6		34	43	51		
		2		175	220	265	ns	
t _{pd}	Propagation delay, MR to output	4.5	12 ⁽¹⁾	35	44	53		
		6		30	37	45		
		2		150	190	225		
t _{pd}	Propagation delay output enable to Q (Figure 6)	4.5	12 ⁽¹⁾	30	38	45	ns	
		6		26	33	38		
		2		60	75	90		
- t	Output transition times	4.5		12	15	18	ns	
		6		10	13	15		
f _{MAX}	Maximum clock frequency	5	60 ⁽¹⁾				MHz	
C _i	Input capacitance			10	10	10	pF	
Co	Three-state output capacitance			10	10	10	pF	
C _{pd} ⁽²⁾ (3)	Power dissipation capacitance	5	29				pF	
HCT TYPES	; ;							
t _{pd}	Propagation delay, clock to output	4.5	17 ⁽¹⁾	40	50	60	ns	
t _{pd}	Propagation delay, MR to output	4.5	18 ⁽¹⁾	44	55	66	ns	
		2		150	190	225		
t _{pd}	Propagation delay output enable to Q (Figure 6)	4.5	14 ⁽¹⁾	30	38	45	ns	
		6		26	33	38		
^l t	Output transition times	4.5		15	19	22	ns	
мах	Maximum clock frequency	5	60 ⁽¹⁾				MHz	
C _i	Input capacitance			10	10	10	pF	
C _{pd} ⁽²⁾ ⁽³⁾	Power dissipation capacitance	5	34				pF	

(1) Typical value tested at 5V, $C_L = 15$ pF.

(2) C_{PD} is used to determine th edynamic power consumption, per package.

(3) $P_D = V_{CC}^2 f_i + \Sigma (C_L V_{CC}^2 + f_0)$ where $f_i = Input$ Frequency, $C_L = Output$ Load Capacitance, $V_{CC} = Supply$ Voltage.



5.6 Prerequisite For Switching Characteristics

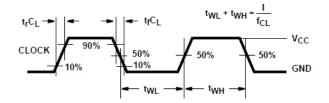
	DADAMETER	V AA	25°C	-40°C to 8	85°C	-55°C to 125°C		UNITS	
	PARAMETER	V _{cc} (V)	MIN MAX	K MIN	MAX	MIN	MAX	UNITS	
HC TYPE	3				I				
		2	6	5		4			
f _{MAX}	Maximum clock frequency	4.5	30	24		20		MHz	
		6	35	28		24			
		2	80	100		120			
t _W	MR pulse width	4.5	16	20		24		ns	
		6	14	17		20			
		2	80	100		120			
t _W	Clock pulse width	4.5	16	20		24		ns	
		6	14	17		20			
		2	60	75		90			
t _{SU}	Set-up time, data to clock and \overline{E} to clock	4.5	12	15		18		ns	
		6	10	13		15			
		2	3	3		3			
t _H	Hold time, data to clock	4.5	3	3		3		ns	
		6	3	3		3			
		2	0	0		0			
t _H	Hold time, \overline{E} to clock	4.5	0	0		0		ns	
		6	0	0		0			
		2	60	75		90			
t _{REM}	Removal time, MR to clock	4.5	12	15		18		ns	
		6	10	13		15			
НСТ ТҮРЕ	ES		1				1		
f _{MAX}	Maximum clock frequency	4.5	20	16		13		MHz	
twtw	MR pulse width	4.5	15	19		22		ns	
t _W	Clock pulse width	4.5	25	31		38		ns	
t _{SU}	Set-up Time, E to clock	4.5	12	15		18		ns	
t _{SU}	Set-up time, data to clock	4.5	18	23		27		ns	
t _H	Hold time, data to clock	4.5	0	0		0		ns	
t _H	Hold time, \overline{E} to clock	4.5	0	0		0		ns	
t _{REM}	Removal time, MR to clock	4.5	12	15		18		ns	



6 Parameter Measurement Information

 t_{PD} is the maximum between t_{PLH} and t_{PHL}

 t_{t} is the maximum between t_{TLH} and t_{THL}



NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{MAX} , input duty cycle = 50%

Figure 6-1. HC clock pulse rise and fall times and pulse width

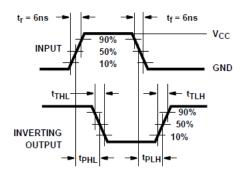
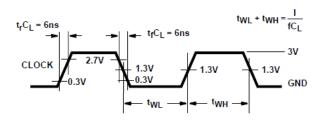
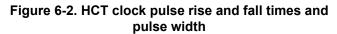


Figure 6-3. HC and HCU transition times and propagation delay times, combination logic



NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. FOr $f_{MAX},$ input duty cycle = 50%



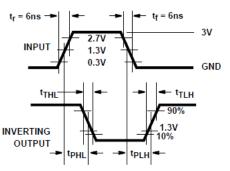
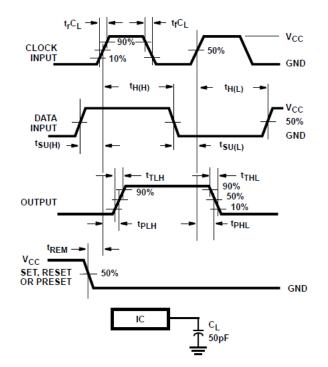
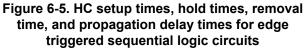
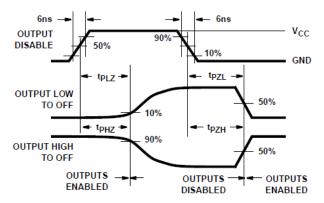


Figure 6-4. HCT transition times and propagation delay times, combination logic



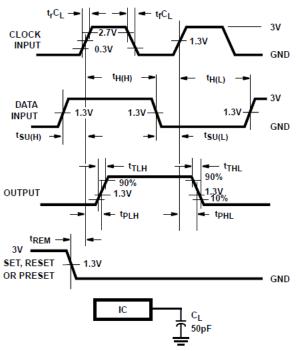


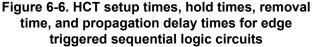


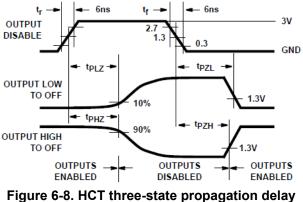




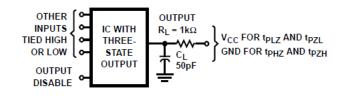








waveform



NOTE: Opend drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output $R_L = 1k\Omega$ to V_{CC} , $C_L = 50pF$

Figure 6-9. HC and HCT three-state propagation delay test circuit



7 Detailed Description

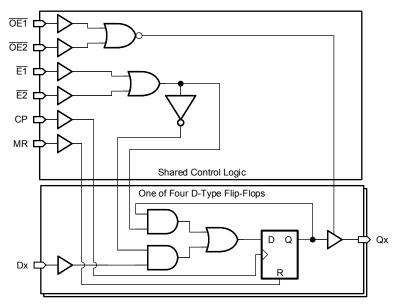
7.1 Overview

The CDx4HC173 or CDx4HCT173 high speed three-state quad Dtype flip-flops are fabricated with silicon gate CMOS technology. They possess the low power consumption of standard CMOS Integrated circuits, and can operate at speeds comparable to the equivalent low power Schottky devices. The buffered outputs can drive 15 LSTTL loads. The large output drive capability and three-state feature make these parts ideally suited for interfacing with bus lines in bus oriented systems

The four D-type flip-flops operate synchronously from a common clock. The outputs are in the three-state mode when either of the two output disable pins are at the logic "1" level. The input ENABLES allow the flip-flops to remain in their present states without having to disrupt the clock If either of the 2 input ENABLES are taken to a logic "1" level, the Q outputs are fed back to the inputs, forcing the flip-flops to remain in the same state. Reset is enabled by taking the RESET (MR) input to a logic "1" level. The data outputs change state on the positive going edge of the clock.

The 'HCT173 logic family is functionally, as well as pin compatible with the standard LS logic family.

7.2 Functional Block Diagram





7.3 Device Functional Modes

	INP		DATA	OUTPUT		
MR	СР	DATA E	NABLE	DAIA	OUTFOI	
INIT	UP .	E1	E2	D	Qn	
Н	Х	Х	Х	Х	L	
L	L	Х	Х	Х	Q ₀	
L	↑	Н	Х	Х	Q ₀	
L	Ť	Х	Н	Х	Q ₀	
L	1	L	L	L	L	
L	Ť	L	L	Н	Н	

Table 7-1. Truth Table⁽¹⁾⁽²⁾

(1) H = High voltage level. L = Low voltage level. X = Irrelevant. ↑ = Transition from low to high level. Q₀ = Level before the indicated steady-state input conditions were established.

(2) When either OE1 or OE2 (or both) is (are) high, the output is disabled to the high-impedance stat, however, sequential operation of the flip-flops is not affected.



8 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- μ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

9 Layout

9.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.



10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

10.1 Documentation Support

10.1.1 Related Documentation

10.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

10.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

10.4 Trademarks

TI E2E[™] is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

10.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
5962-8682501EA	Active	Production	CDIP (J) 16	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-8682501EA CD54HC173F3A
5962-8875901EA	Active	Production	CDIP (J) 16	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-8875901EA CD54HCT173F3A
CD54HC173F	Active	Production	CDIP (J) 16	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	CD54HC173F
CD54HC173F.A	Active	Production	CDIP (J) 16	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	CD54HC173F
CD54HC173F3A	Active	Production	CDIP (J) 16	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-8682501EA CD54HC173F3A
CD54HC173F3A.A	Active	Production	CDIP (J) 16	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-8682501EA CD54HC173F3A
CD54HCT173F3A	Active	Production	CDIP (J) 16	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-8875901EA CD54HCT173F3A
CD54HCT173F3A.A	Active	Production	CDIP (J) 16	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-8875901EA CD54HCT173F3A
CD74HC173E	Active	Production	PDIP (N) 16	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-55 to 125	CD74HC173E
CD74HC173E.A	Active	Production	PDIP (N) 16	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-55 to 125	CD74HC173E
CD74HC173M	Obsolete	Production	SOIC (D) 16	-	-	Call TI	Call TI	-55 to 125	HC173M
CD74HC173M96	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC173M
CD74HC173M96.A	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC173M
CD74HC173PW	Obsolete	Production	TSSOP (PW) 16	-	-	Call TI	Call TI	-55 to 125	HJ173
CD74HC173PWR	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-55 to 125	HJ173
CD74HC173PWR.A	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HJ173
CD74HCT173E	Active	Production	PDIP (N) 16	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-55 to 125	CD74HCT173E
CD74HCT173E.A	Active	Production	PDIP (N) 16	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-55 to 125	CD74HCT173E
CD74HCT173M	Obsolete	Production	SOIC (D) 16	-	-	Call TI	Call TI	-55 to 125	HCT173M
CD74HCT173M96	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT173M
CD74HCT173M96.A	Active	Production	SOIC (D) 16	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT173M

⁽¹⁾ **Status:** For more details on status, see our product life cycle.



PACKAGE OPTION ADDENDUM

15-Jul-2025

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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OTHER QUALIFIED VERSIONS OF CD54HC173, CD54HCT173, CD74HC173, CD74HCT173 :

• Catalog : CD74HC173, CD74HCT173

• Military : CD54HC173, CD54HCT173

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications



Texas

STRUMENTS

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD74HC173M96	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
CD74HC173PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
CD74HCT173M96	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1



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PACKAGE MATERIALS INFORMATION

7-Aug-2025



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CD74HC173M96	SOIC	D	16	2500	353.0	353.0	32.0
CD74HC173PWR	TSSOP	PW	16	2000	356.0	356.0	35.0
CD74HCT173M96	SOIC	D	16	2500	340.5	336.1	32.0

TEXAS INSTRUMENTS

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7-Aug-2025

TUBE



- B - Alignment groove width

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
CD74HC173E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HC173E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HC173E.A	N	PDIP	16	25	506	13.97	11230	4.32
CD74HC173E.A	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT173E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT173E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT173E.A	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT173E.A	N	PDIP	16	25	506	13.97	11230	4.32

D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.



J (R-GDIP-T**) 14 LEADS SHOWN

CERAMIC DUAL IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

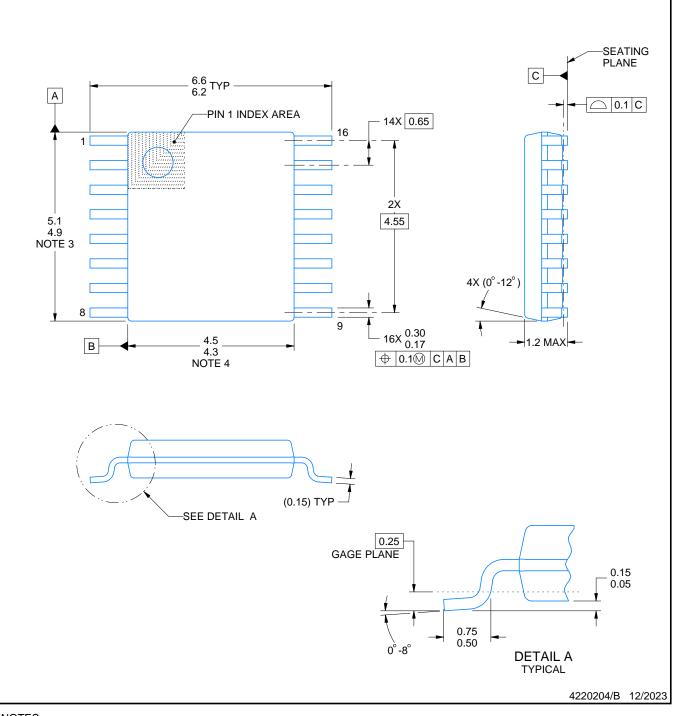
PW0016A



PACKAGE OUTLINE

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.

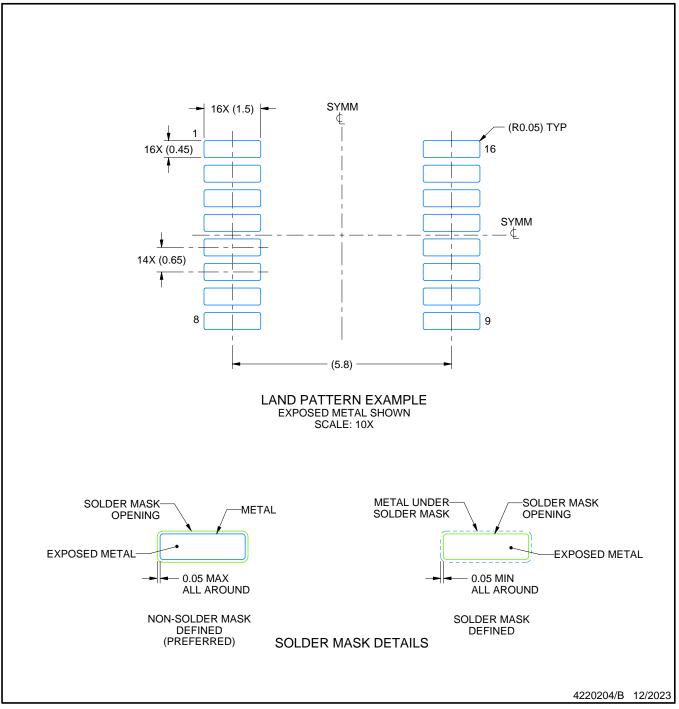


PW0016A

EXAMPLE BOARD LAYOUT

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

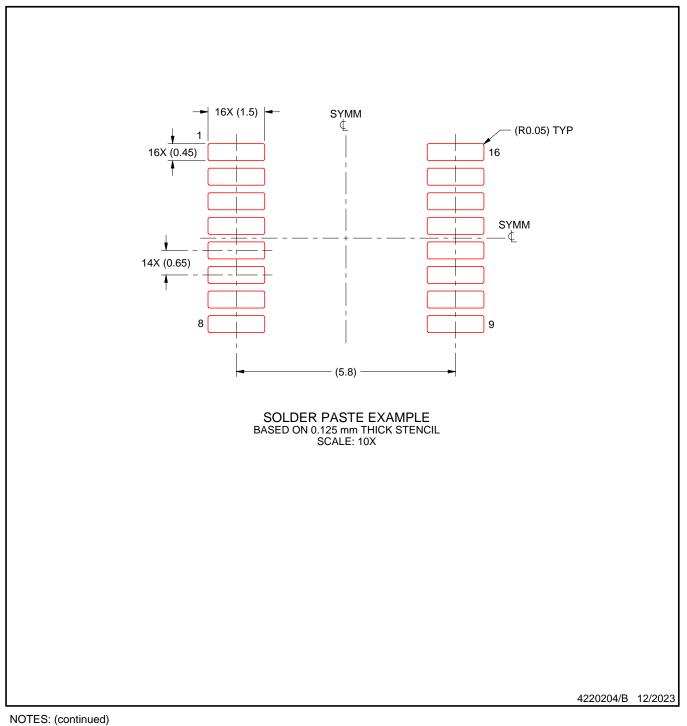


PW0016A

EXAMPLE STENCIL DESIGN

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE





^{8.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{9.} Board assembly site may have different recommendations for stencil design.

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- \triangle The 20 pin end lead shoulder width is a vendor option, either half or full width.



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